

--BACKGROUND OF THE INVENTION--.

Between lines 1 and 2, insert the sub-heading --Field of the Invention--.

Line 5, change the heading "BACKGROUND OF THE INVENTION" to

--DESCRIPTION OF THE BACKGROUND ART--.

Line 20, change "filed" to --field--.

Page 2

Line 21, change "more" to --further--.

Line 24, change "part" to --parts--.

Page 3

Line 7, change the heading "OBJECTS OF THE INVENTION" to --SUMMARY  
OF THE INVENTION--.

Line 18, delete the heading "SUMMARY OF THE INVENTION".

Page 4

Line 15, change "amorphousness" to --amorphous--.

Page 6

Line 12, change "filed" to --field--.

Page 8

Line 13, change "filed" to --field--.

Page 11

Line 8, change "amorphousness" to --amorphous--.

Line 14, change "filed" to --field--.

Page 12

Line 24, change "130" to --230--.

Page 13

Line 17, change "212" to --222--.

Page 14

Line 21, change "filed" to --field--.

Page 15

Line 10, change "Co" to --Ti--.

Page 16

Line 18, change "312" to --322--.

Page 17

Line 16, change "filed" to --field--.

Page 20

Line 17, change "filed" to --field--.

**In the Claims:**

Please amend the claims as follows:

1. (Amended) A method for fabricating a semiconductor device using a silicide (self aligned silicide) process, comprising [the steps of]:
- providing a material to be silicided at least on [the] a surface of [an area] the semiconductor device that is to be silicided;